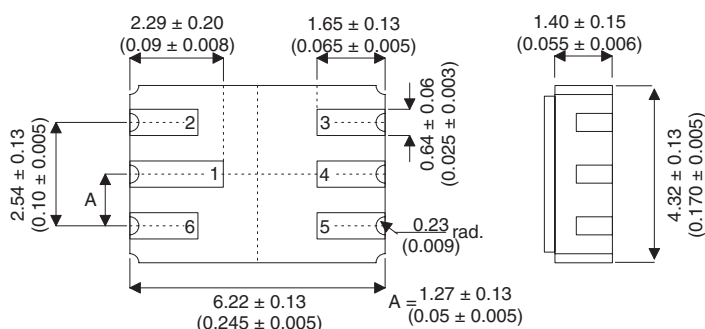


MECHANICAL DATA

Dimensions in mm (inches)



**LCC2 PACKAGE
(MO-041BB)**

Underside View

- PAD 1 – Collector 1
- PAD 2 – Base 1
- PAD 3 – Base 2
- PAD 4 – Collector 2
- PAD 5 – Emitter 2
- PAD 6 – Emitter 1

**DUAL PNP SILICON TRANSISTORS
IN A HERMETICALLY SEALED
CERAMIC SURFACE MOUNT
PACKAGE FOR HIGH RELIABILITY
APPLICATIONS**

FEATURES

- High Voltage Switching
- Low Power Amplifier Applications
- Hermetic Ceramic Surface Mount Package

APPLICATIONS

- General Purpose
- High Speed Saturated Switching
- Screening Options Available

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CEO}	Collector – Emitter Voltage	-175V
V_{CBO}	Collector – Base Voltage	-175V
V_{EBO}	Emmitter – Base Voltage	-5V
I_C	Collector Current	-1A
P_D	Total Device Dissipation @ $T_A = 25^{\circ}C$	500mW
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to +200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
BV_{CEO}	Collector–Emitter Breakdown Voltage ¹	$I_C = -10\text{mA}$ $I_B = 0$	-175		V
BV_{CBO}	Collector – Base Breakdown Voltage ¹	$I_C = -100\mu\text{A}$ $I_E = 0$	-175		
BV_{EBO}	Emitter – Base Breakdown Voltage ¹	$I_C = 0$ $I_E = -10\mu\text{A}$	-5.0		
I_{EBO}	Emitter Cut-off Current	$V_{BE} = -3.0\text{V}$ $I_C = 0$		-50	nA
I_{CBO}	Collector Cut-off Current	$V_{CB} = -100\text{V}$ $I_E = 0$		-100	
ON CHARACTERISTICS					
h_{FE}	DC Current Gain ¹	$I_C = -0.1\text{mA}$ $V_{CE} = -10\text{V}$	80		–
		$I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}$	90		
		$I_C = -10\text{mA}$ $V_{CE} = -10\text{V}$	100		
		$I_C = -50\text{mA}$ $V_{CE} = -10\text{V}$	100	300	
		$I_C = -150\text{mA}$ $V_{CE} = -10\text{V}$	50		
$V_{CE(sat)}$	Collector – Emitter Saturation Voltage ¹	$I_C = -10\text{mA}$ $I_B = -1.0\text{mA}$		-0.3	V
		$I_C = -50\text{mA}$ $I_B = -5\text{mA}$		-0.5	
$V_{BE(sat)}$	Base – Emitter Saturation Voltage ¹	$I_C = -10\text{mA}$ $I_B = -1.0\text{mA}$		-0.8	V
		$I_C = -50\text{mA}$ $I_B = -5\text{mA}$	-0.65	-0.9	
SMALL SIGNAL CHARACTERISTICS					
f_t	Current Gain Bandwidth Product	$V_{CE} = -30\text{V}$ $I_C = -30\text{mA}$ $f = 100\text{MHz}$	100		MHz
C_{ob}	Output Capacitance	$V_{CB} = -20\text{V}$ $I_E = 0$ $f = 100\text{kHz}$		10	pF
C_{ib}	Input Capacitance	$V_{BE} = 1.0\text{V}$ $I_C = 0$ $f = 100\text{kHz}$		75	pF
h_{ie}	Input Impedance	$V_{CE} = -10\text{V}$ $I_C = -10\text{mA}$ $f = 1.0\text{kHz}$	200		1200 Ω
h_{re}	Voltage Feedback Ratio				3.0 $\times 10^{-4}$
h_{fe}	Small Signal Current Gain		80		320 —
h_{oe}	Output Admittance				200 μmhos
NF			$V_{CE} = -10\text{V}$ $I_C = -0.5\text{mA}$ $R_S = 1.0\Omega$ $f = 1.0\text{kHz}$		
SWITCHING CHARACTERISTICS					
t_{on}	Turn–On Time	$V_{CC} = -100\text{V}$ $V_{BE} = 4.0\text{V}$		400	ns
t_{off}	Turn–Off Time	$I_C = -50\text{mA}$ $I_{B1} = I_{B2} = -5\text{mA}$		600	

1) Pulse test : Pulse Width < 300 μs ,Duty Cycle < 2%

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